

**PRE-BIASED (R1 = R2) SMALL SIGNAL SURFACE MOUNT 100mA NPN TRANSISTOR**
**Features**

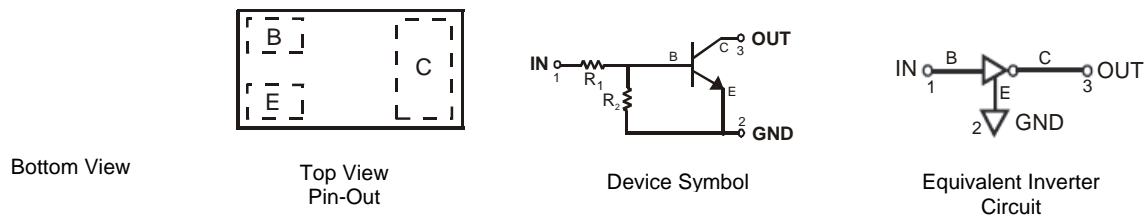
- Epitaxial Planar Die Construction
- Ultra-Small Leadless Surface Mount Package
- Ideally Suited for Automated Assembly Processes
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Part Number	R1 (NOM)	R2 (NOM)	Marking
DDTC114ELP	10K	10K	N5

**Mechanical Data**

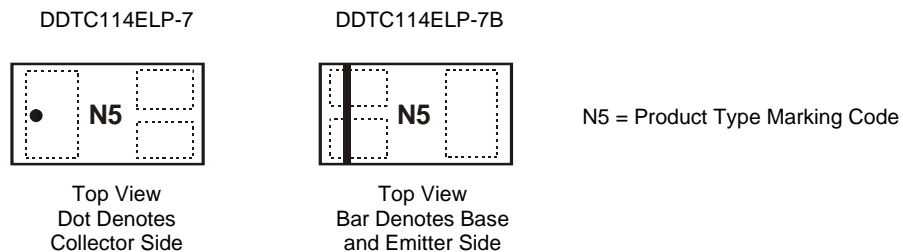
- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0009 grams (approximate)

DFN1006-3


**Ordering Information** (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DDTC114ELP-7	N5	7	8	3,000
DDTC114ELP-7B	N5	7	8	10,000

- Notes:
1. No purposefully added lead.
  2. Diodes Inc's "Green" policy can be found on our website at <http://www.diodes.com>.
  3. For packaging details, go to our website at <http://www.diodes.com>.

**Marking Information**


**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub>	50	V
Input Voltage	V <sub>IN</sub>	-10 to +40	V
Output Current	I <sub>O</sub>	50	mA
Collector Current	I <sub>C(MAX)</sub>	100	mA

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P <sub>D</sub>	250	mW
Power Derating above 25°C	P <sub>der</sub>	2	mW/°C
Thermal Resistance, Junction to Ambient Air (Note 4) (Equivalent to one heated junction of NPN)	R <sub>θJA</sub>	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>Off Characteristics (Note 5)</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	50	—	—	V	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	50	—	—	V	I <sub>C</sub> = 1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5	—	—	V	I <sub>E</sub> = 50μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CEX</sub>	—	—	0.5	μA	V <sub>CE</sub> = 50V, V <sub>EB(OFF)</sub> = 3.0V
Base Cutoff Current (I <sub>BEX</sub> )	I <sub>BL</sub>	—	—	0.5	μA	V <sub>CE</sub> = 50V, V <sub>EB(OFF)</sub> = 3.0V
Collector-Base Cut Off Current	I <sub>CBO</sub>	—	—	0.5	μA	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0
Collector-Emitter Cut Off Current, I <sub>O(OFF)</sub>	I <sub>CEO</sub>	—	—	1	μA	V <sub>CB</sub> = 50V, I <sub>B</sub> = 0
Emitter-Base Cut Off Current	I <sub>EBO</sub>	—	—	0.4	mA	V <sub>EB</sub> = 4V, I <sub>C</sub> = 0
Input Off Voltage	V <sub>I(off)</sub>	—	1.16	0.5	V	V <sub>CC</sub> = 5V, I <sub>O</sub> = 100uA
<b>On Characteristics (Notes 5 &amp; 6)</b>						
DC Current Gain	h <sub>FE</sub>	10	—	—	—	V <sub>CE</sub> = 5V, I <sub>C</sub> = 1mA
		15	—	—	—	V <sub>CE</sub> = 5V, I <sub>C</sub> = 2mA
		60	—	—	—	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA
		100	—	—	—	V <sub>CE</sub> = 5V, I <sub>C</sub> = 50mA
		90	—	—	—	V <sub>CE</sub> = 5V, I <sub>C</sub> = 70mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	—	0.15	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA
		—	—	0.2	V	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5mA
		—	—	0.25	V	I <sub>C</sub> = 50mA, I <sub>B</sub> = 2.5mA
		—	—	0.25	V	I <sub>C</sub> = 50mA, I <sub>B</sub> = 10mA
		—	—	0.3	V	I <sub>C</sub> = 70mA, I <sub>B</sub> = 10mA
Base-Emitter Turn-On Voltage	V <sub>BE(on)</sub>	—	—	0.85	V	V <sub>CE</sub> = 5V, I <sub>C</sub> = 2mA
		—	—	0.95	V	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	—	—	0.98	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA, V <sub>CE</sub> = 5V
		—	—	1.2	V	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5mA, V <sub>CE</sub> = 5V
Input-On Voltage	V <sub>I(on)</sub>	2.5	1.6	—	V	V <sub>O</sub> = 0.3V, I <sub>O</sub> = 50mA
Input Current	I <sub>I</sub>	—	—	0.88	mA	V <sub>I</sub> = 5V
Output On Voltage (Same as V <sub>CE(sat)</sub> )	V <sub>O(on)</sub>	—	—	0.3	V	I <sub>I</sub> = 2.5mA, I <sub>O</sub> = 50mA
Input Resistance	R <sub>1</sub>	7	10	13	KΩ	—
Resistance Ratio	(R <sub>2</sub> /R <sub>1</sub> )	0.8	1	1.2	—	—
<b>Small Signal Characteristics</b>						
Current Gain-Bandwidth Product	f <sub>T</sub>	—	250	—	MHz	V <sub>CE</sub> = 10V, I <sub>E</sub> = 5mA, f = 1MHz

- Notes: 4. Device mounted on FR-4 PCB, 1" x 0.85" x 0.062"  
5. Short duration pulse test used to minimize self-heating effect. Pulse Test: Pulse width tp < 300 μs, Duty Cycle, d ≤ 2%.  
6. Guaranteed by design.

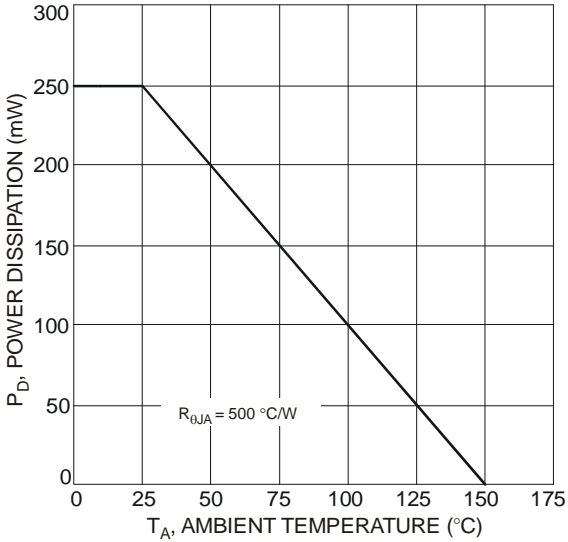


Fig. 1 Power Dissipation vs. Ambient Temperature

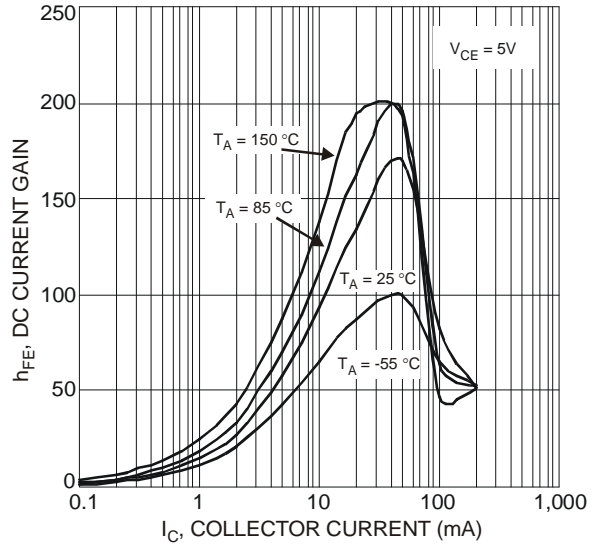


Fig. 2 Typical DC Current Gain vs. Collector Current

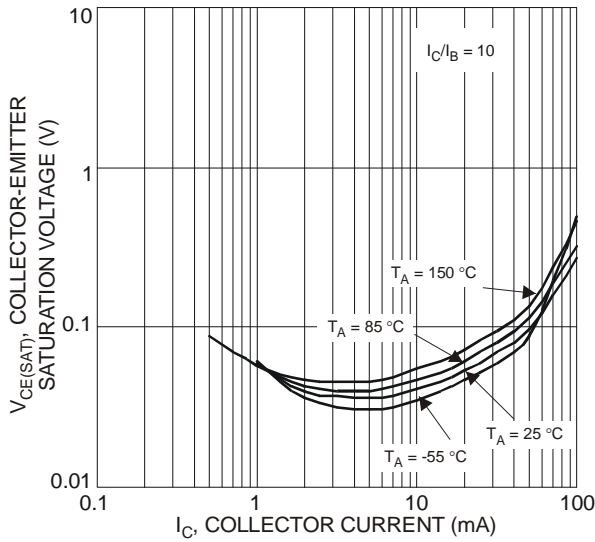


Fig. 3 Typical Collector Emitter Saturation Voltage vs. Collector Current

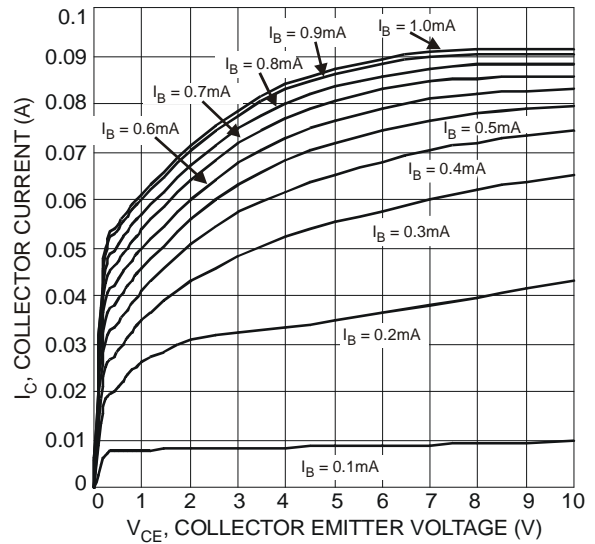


Fig. 4 Typical Collector Current vs. Collector Emitter Voltage

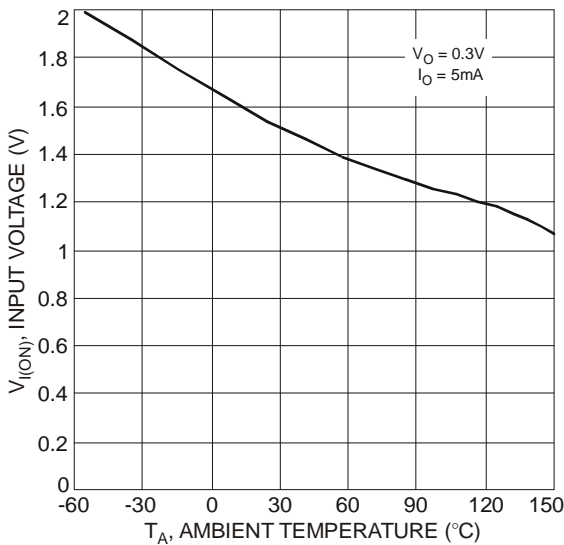


Fig. 5 Typical Input Voltage vs. Ambient Temperature

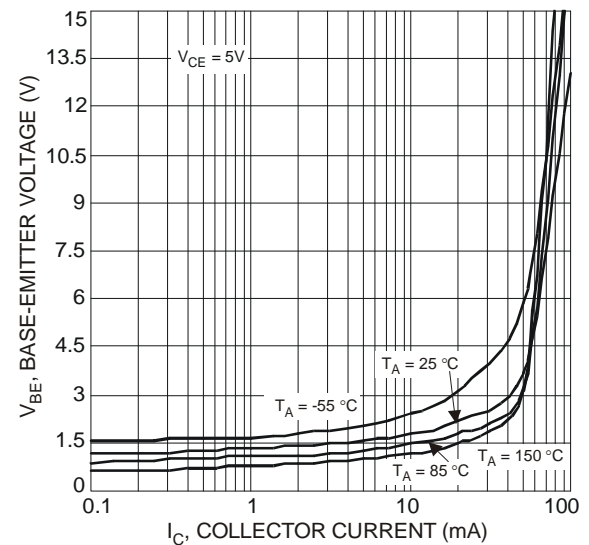


Fig. 6 Typical Base-Emitter Voltage vs. Collector Current

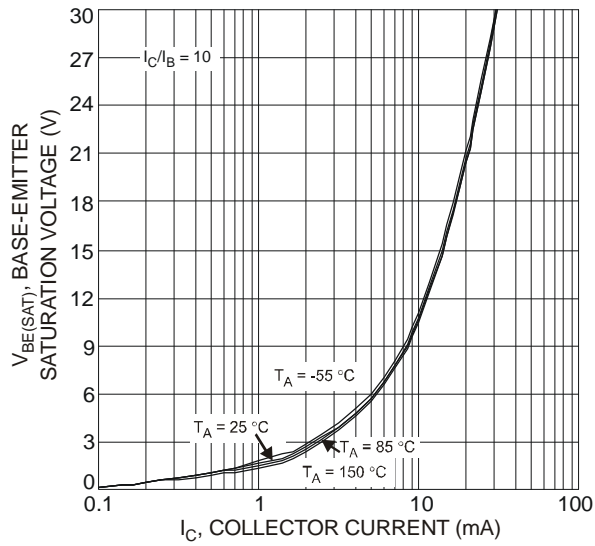
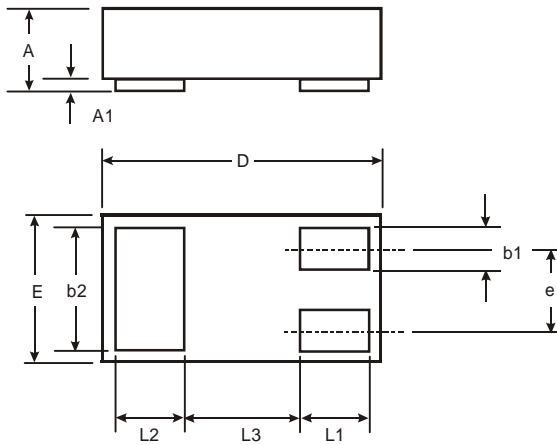


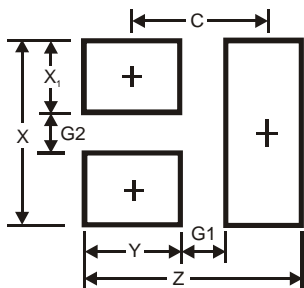
Fig. 7 Typical Base Emitter Saturation Voltage vs. Collector Current

**Package Outline Dimensions**



DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

**IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

**LIFE SUPPORT**

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2011, Diodes Incorporated

[www.diodes.com](http://www.diodes.com)